

# Nobuo Haneji

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6990300/publications.pdf>

Version: 2024-02-01

10  
papers

86  
citations

1684188

5  
h-index

1588992

8  
g-index

10  
all docs

10  
docs citations

10  
times ranked

46  
citing authors

#	ARTICLE	IF	CITATIONS
1	Possible observation of Pb0and Pb1centers at irradiated (100)Si/SiO2interface from electrical measurements. Applied Physics Letters, 1991, 59, 3416-3418.	3.3	40
2	Observation of Giant Electrorefractive Effect in Five-Layer Asymmetric Coupled Quantum Wells (FACQWs). Japanese Journal of Applied Physics, 2004, 43, L1540-L1542.	1.5	16
3	Fabrication and Optical Characterization of Five-Layer Asymmetric Coupled Quantum Well (FACQW). Japanese Journal of Applied Physics, 2002, 41, 2701-2706.	1.5	11
4	Electrical and Thermal Stability Characteristics of HfCN Films as Metal Gate-Electrode Synthesized by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2005, 44, L1019-L1021.	1.5	7
5	Modified five-layer asymmetric coupled quantum well (M-FACQW) for giant negative refractive index change. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 28, 507-513.	2.7	6
6	Improved Etched Surface Morphology in Electron Cyclotron Resonance-Reactive Ion Etching of GaN by Cyclic Injection of CH4/H2/Ar and O2with Constant Ar Flow. Japanese Journal of Applied Physics, 2005, 44, 5819-5823.	1.5	2
7	Preparation of Amorphous Fluorinated Carbon Film Using Low Global-Warming Potential Gas, C4F6, by Plasma Enhanced Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, L151-L153.	1.5	2
8	Influence of Heterointerface Abruptness on Electrorefractive Effect in InGaAs/InAlAs Five-Layer Asymmetric Coupled Quantum Well. Japanese Journal of Applied Physics, 2010, 49, 04DG04.	1.5	2
9	Proposal of Ge/SiGe five-layer asymmetric coupled quantum well for mach-zehnder modulators. , 2009, , .		0
10	Considerations on the Transient Thermal Impedance of Semiconductor valves. IEEJ Transactions on Electronics, Information and Systems, 1989, 109, 515-522.	0.2	0